

**Amendment to the Specification**

Please replace the following paragraph on pages 8-9, paragraph 0023, with the following clean replacement paragraph:

The masses 24, 26 and 28 of the Figure together define at least a portion of a capacitor construction. Such capacitor construction can be incorporated into various semiconductor devices, such as, for example, a DRAM cell. In embodiments in which the capacitor construction is incorporated into a DRAM cell, there will typically be a transistor gate (not shown) utilizing diffusion region 16 as a source/drain region, and accordingly electrically connected to mass 24 ~~though~~ through diffusion region 16. In such embodiments, mass 24 can be considered a storage node of a capacitor construction.